

Zhe Ashley Jian

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

115
citations

1478505

6
h-index

1474206

9
g-index

10
all docs

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docs citations

10
times ranked

165
citing authors

#	ARTICLE	IF	CITATIONS
1	Demonstration of atmospheric plasma activated direct bonding of N-polar GaN and \hat{I}^2 -Ga ₂ O ₃ (001) substrates. Applied Physics Letters, 2022, 120, .	3.3	2
2	Switching Performance Analysis of 3.5 kV Ga ₂ O ₃ Power FinFETs. IEEE Transactions on Electron Devices, 2021, 68, 672-678.	3.0	12
3	Characterization of MOCVD-grown AlSiO gate dielectric on \hat{I}^2 -Ga ₂ O ₃ (001). Applied Physics Letters, 2021, 118, .	3.3	10
4	Investigation and optimization of HfO ₂ gate dielectric on N-polar GaN: Impact of surface treatments, deposition, and annealing conditions. Applied Physics Letters, 2021, 119, .	3.3	9
5	Improved operational reliability of MOCVD-grown AlSiO gate dielectric on \hat{I}^2 -Ga ₂ O ₃ (001) by post-metallization annealing. Semiconductor Science and Technology, 2021, 36, 09LT03.	2.0	3
6	Design of ultra-scaled-channel N-polar GaN HEMTs with high charge density: A systematic study of hole traps and their impact on charge density in the channel. Journal of Applied Physics, 2020, 128, .	2.5	5
7	Deep UV-assisted capacitance-voltage characterization of post-deposition annealed Al ₂ O ₃ / \hat{I}^2 -Ga ₂ O ₃ (001) MOSCAPs. Applied Physics Letters, 2020, 116, .	3.3	14
8	Temperature-dependent current-voltage characteristics of \hat{I}^2 -Ga ₂ O ₃ trench Schottky barrier diodes. Applied Physics Letters, 2020, 116, .	3.3	41
9	Chlorine-based inductive coupled plasma etching of \hat{I}^2 -Ga ₂ O ₃ . Semiconductor Science and Technology, 2019, 34, 035006.	2.0	15
10	HfO ₂ as gate insulator on N-polar GaN-AlGa _n heterostructures. Semiconductor Science and Technology, 0, .	2.0	4